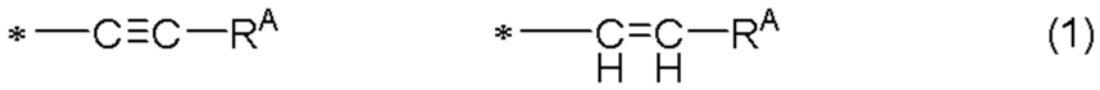
TITLE OF INVENTION: WAFER EDGE PROTECTION FILM FORMING METHOD, PATTERNING PROCESS, AND COMPOSITION FOR FORMING WAFER EDGE PROTECTION FILM

ABSTRACT

The present invention provides a wafer edge protection film having dry etching resistance superior to those of the previously-known wafer edge protection films, as well as excellent film forming property even at wafer edge portions, which are difficult to coat: a wafer edge protection film forming method for forming a protection film on a wafer edge of a substrate, including the steps of (i) coating a peripheral edge of the substrate with a composition for forming a protection film including an aromatic ring-containing resin (A) having an organic group represented by the following general formula (1), and a solvent; and (ii) curing the applied composition for forming a protection film by heat or optical irradiation to form the protection film on the peripheral edge of the substrate.



(1)

wherein R^A is a hydrogen atom or a monovalent organic group having 1 to 10 carbon atoms, and * represents a bonding site.

[FIG. 1]